

Product data sheet

1. Product profile

1.1 General description

Planar PIN diode in a SOD882T leadless ultra small plastic SMD package.

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1.2 Features

- High speed switching for RF signals
- Low diode capacitance
- Low forward resistance
- Very low series inductance
- For applications up to 3 GHz

1.3 Applications

RF attenuators and switches

2. Pinning information

Table 1. Discrete pinning

Pin	Description	Simplified outline	Symbol
1	cathode	<u>[1]</u>	
2	anode	Transparent top view	₩ -

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BAP63LX	-	leadless ultra small plastic package; 2 terminals; body 1 \times 0.6 \times 0.4 mm	SOD882T		



Silicon PIN diode

4. Marking

Table 3. Marking

Type number	Marking code
BAP63LX	LD

5. Limiting values

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Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	50	V
I _F	forward current		-	100	mA
P _{tot}	total power dissipation	$T_{sp} = 90 ^{\circ}C$	-	135	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		78	K/W

7. Characteristics

Table 6. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 50 \text{ mA}$	-	0.95	1.1	V
I_R	reverse current	V _R = 20 V	-	-	10	nA
C _d diode capacitance	see Figure 1; f = 1 MHz;					
		$V_R = 0 V$	-	0.34	-	pF
		$V_R = 1 V$	-	0.29	-	pF
		$V_{R} = 20 \text{ V}$	-	0.24	0.30	pF
r _D diode forward resistance	see Figure 2; f = 100 MHz;					
		$I_F = 0.5 \text{ mA}$	-	2.3	3.3	Ω
		$I_F = 1 \text{ mA}$	-	1.87	3.0	Ω
		$I_F = 10 \text{ mA}$	-	1.19	1.8	Ω
		$I_F = 100 \text{ mA}$	-	0.93	1.5	Ω
ISL	isolation	see Figure 3; V _R = 0 V;				
		f = 900 MHz	-	15.9	-	dB
		f = 1800 MHz	-	10.5	-	dB
		f = 2450 MHz	-	8.3	-	dB
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Table 6. Characteristics ...continued

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L _{ins}	L _{ins} insertion loss	see Figure 4; $I_F = 0.5 \text{ mA}$;				
		f = 900 MHz	-	0.20	-	dB
		f = 1800 MHz	-	0.20	-	dB
		f = 2450 MHz	-	0.21	-	dB
L _{ins} eet4U.com	insertion loss	see Figure 4; I _F = 1 mA;				
		f = 900 MHz	-	0.17	-	dB
		f = 1800 MHz	-	0.17	-	dB
		f = 2450 MHz	-	0.19	-	dB
L _{ins}	L _{ins} insertion loss	see Figure 4; I _F = 10 mA;				
		f = 900 MHz	-	0.12	-	dB
		f = 1800 MHz	-	0.13	-	dB
		f = 2450 MHz	-	0.15	-	dB
L _{ins}	insertion loss	see Figure 4; I _F = 100 mA;				
		f = 900 MHz	-	0.11	-	dB
		f = 1800 MHz	-	0.11	-	dB
		f = 2450 MHz	-	0.15	-	dB
τ∟	charge carrier life time	when switched from I _F = 10 mA to I _R = 6 mA; R _L = 100 Ω ; measured at I _R = 3 mA	-	0.32	-	μs
L _S	series inductance	I _F = 100 mA; f = 100 MHz	-	0.4	-	nΗ

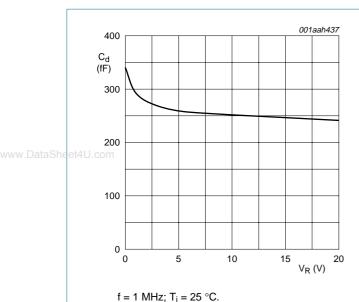


Fig 1. Diode capacitance as a function of reverse voltage; typical values

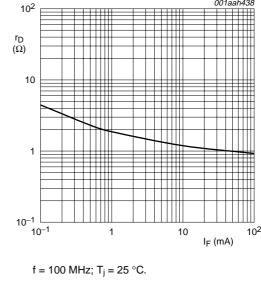
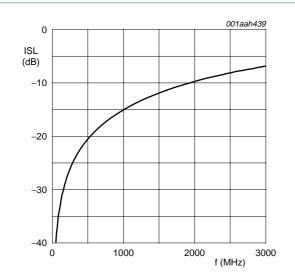
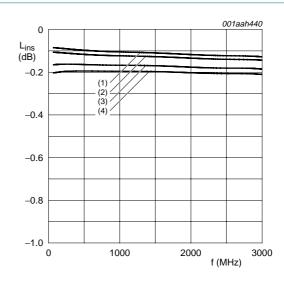


Fig 2. Forward resistance as a function of forward current; typical values



T_{amb} = 25 °C

Diode zero biased and inserted in series with a 50 Ω stripline circuit



T_{amb} = 25 °C

- (1) $I_F = 100 \text{ mA}$
- (2) $I_F = 10 \text{ mA}$
- (3) $I_F = 1 \text{ mA}$
- (4) $I_F = 0.5 \text{ mA}$

Diode inserted in series with a 50 Ω stripline circuit and biased via the analyzer Tee network

Fig 4. Insertion loss of the diode as a function of frequency; typical values

Fig 3. Isolation of the diode as a function of frequency; typical values

8. Package outline

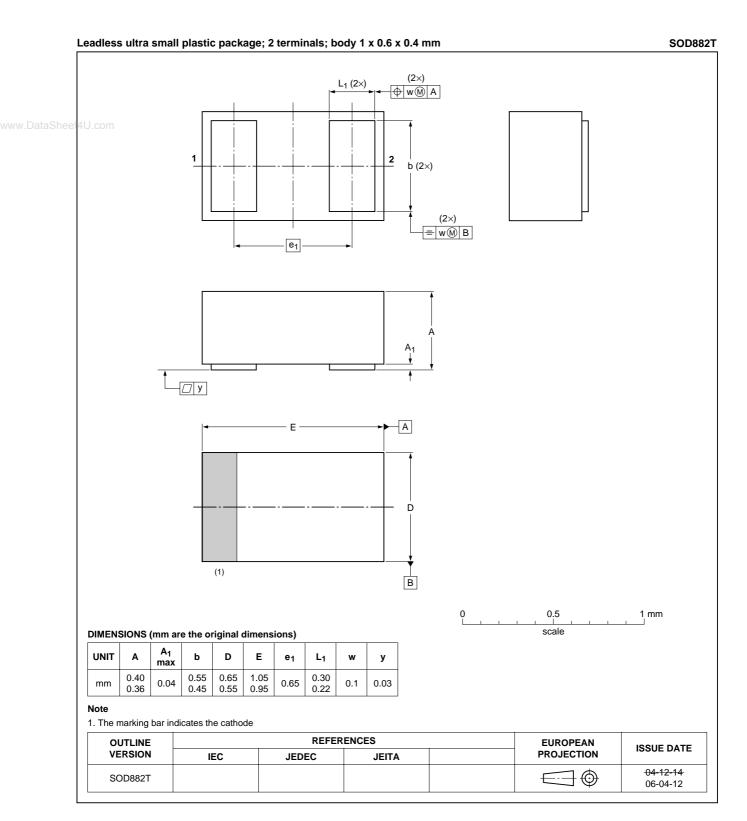


Fig 5. Package outline SOD882T

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9. Abbreviations

Table 7. Abbreviations

Acronym	Description
PIN	P-type, Intrinsic, N-type
SMD	Surface Mounted Device
RF	Radio Frequency

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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP63LX_1	20071211	Product data sheet	-	-

Silicon PIN diode

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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Date of release: 11 December 2007 Document identifier: BAP63LX_1

